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IXYS Introduces Half-Bridge MOSFET Modules in ISOPLUS i4-PAC™

Milpitas, CA, January 14, 2009 - IXYS Corporation (NASDAQ: IXYS) announces the release of half-bridge MOSFET modules that are available in IXYS' proprietary ISOPLUS i4-PAC™ packaging. These modules provide unsurpassed thermal performance and temperature cycling capabilities making them ideal for applications implementing heat sink grounding techniques. These devices are also suitable for designers who seek isolated half-bridge configurations integrated into one single package avoiding the use of multiple discrete devices thus promoting critical board layout space savings.

The i4-PAC™ is a UL recognized isolated package incorporating a direct copper bond (DCB) ceramic isolator which provides 2500Vrms isolation with superior thermal performance. In comparison with conventional package housings, the ISOPLUS i4-PAC yielded as high as a 45% decrease in thermal resistance. These modules exhibit excellent switching behavior due to low inductive current paths as dice are located within one package. An additional feature includes a reduction in EMI emissions due to the low coupling capacitance between die and heat sink. These half-bridge modules take full advantage of proven technology platforms commonly implemented in both the IXYS Trench and Polar discrete MOSFET product families.

These new modules are currently available in two configurations. One configuration (part number prefix denoted as FMP) combines carefully selected P-Channel and N-Channel MOSFETs configured in a phase-leg or half-bridge topology with a common drain arrangement. An added benefit from this configuration is the elimination of gate drive circuitry normally required in driving an N-Channel MOSFET on the high-side of a phase leg, resulting in a component count reduction, thus improving drive circuit simplicity, space savings and over-all component cost. The other configuration (part number prefix denoted as FMM) is comprised of two N-Channel MOSFETs situated on both the low and high side of the phase leg.

The Dual N-Channel FMM modules are capable of accommodating drain to source breakdown voltages of 200V, 250V, 500V and 600V with drain current values from 12 amperes to 33 amperes. The P&N FMP modules are available to support applications requiring drain to source breakdown voltages of 100V, 150V and 200V with drain current ratings from 17 amperes to 54 amperes.

A broad range of applications stand to benefit from these new half-bridge MOSFET modules. These applications include DC/AC motor drives, uninterruptible power supplies, switch mode power supplies, solar/wind power inverters, synchronous rectifiers, industrial battery chargers, Class AB audio amplifiers and multi-phase DC to DC converters. Initial device offerings include part numbers: FMM60-02TF, FMM50-025TF, FMM22-05PF, FMM22-06PF, FMP26-02P, FMP36-015P, and FMP76-010T.

Additional product information may be obtained by visiting IXYS website at [://www.ixys.com](http://www.ixys.com), or by contacting the company directly.

About IXYS Corporation

IXYS Corporation makes and markets technology-driven products to improve power conversion efficiency, generate solar and wind power and provide efficient motor control for industrial applications. IXYS offers a diversified product base that addresses worldwide needs for power control, electrical efficiency, renewable energy, telecommunications, medical devices, electronic displays and RF power.

Safe Harbor Statement

Any statements contained in this press release that are not statements of historical fact, including the performance, rating, availability, reliability and suitability of products for various applications, may be deemed to be forward-looking statements. There are a number of important factors that could cause the results of IXYS to differ materially from those indicated by these forward-looking statements, including, among others, risks detailed from time to time in the Company's SEC reports, including its Form 10-Q for the quarter ended September 30, 2008. The Company undertakes no obligation to publicly release the results of any revisions to these forward-looking statements.